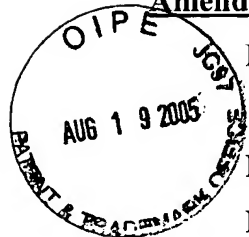


Amendments to the Specification:



Page 7, after line 2, insert the following new paragraphs:

Fig. 5 is a detailed illustration of Figure 2.

Fig. 6 is a detailed illustration of Figure 3.

Page 8, lines 4-17, replace paragraph [026] with the following amended paragraph:

[026] Fig. 5 ~~in~~ shows one embodiment[[,]] of the present invention, wherein a pulse generator 70 includes a TLP generator 71 ~~(not shown)~~ and a biasing source 72 ~~(not shown)~~. The TLP generator provides a first ESD-scale pulse to first terminal 62 and a second terminal 64 of semiconductor device 60. The biasing source provides a second ESD-scale pulse to a second terminal 64 and a third terminal 66 of semiconductor device 60. In an embodiment wherein semiconductor device 60 is a MOS transistor, first terminal 62 and second terminal 64 are respectively a drain and a source of the MOS transistor, and third terminal 66 is the gate or substrate of the MOS transistor. In an embodiment wherein semiconductor device 60 is a SCR or LVTSCR, first terminal 62 and second terminal 64 are respectively an anode and a cathode of the SCR or LVTSCR, and third terminal 66 is the substrate or semiconductor well region of the SCR or LVTSCR. In an embodiment wherein semiconductor device 60 is a BJT or FOD, first terminal 62 and second terminal 64 are respectively a collector and an emitter of the BJT or FOD, and third terminal 66 is a base of the BJT or FOD.

Page 9, lines 7-20, replace paragraph [029] with the following amended paragraph:

[029] Fig. 3 is a simplified schematic block diagram of a system 90 for measuring ESD characteristics of a semiconductor device 60 in accordance with another embodiment of the present invention. Referring to ~~Fig. 3~~ Fig. 6, system 90 includes semiconductor device 60, a switching device 92, pulse generator 70, a detector 94, a data collector 96 and a computer 98. In one embodiment, switching device 92 is a switching matrix that switches a connection to

semiconductor device 60 between detector 94 and pulse generator 70. Detector 94 includes an electrical analyzer (~~not shown~~) such as the HP 4155 analyzer manufactured by Hewlett Packard Company. When detector 94 is electrically connected to semiconductor device 60 by switching device 92, detector 94 provides a signal, for example, a direct current (DC) signal, to semiconductor device 60 to detect whether a leakage current flows in semiconductor device 60. If detector 94 detects a leakage current, semiconductor device 60 is determined as having failed. If no leakage current is detected, pulse generator 70 switches to semiconductor device 60 for subsequent measurements.

Page 9, line 21 through page 10, line 4, replace paragraph [030] with the following amended paragraph:

[030] Data collector 96, for example, an oscilloscope, collects voltage and current data regarding ESD characteristics of semiconductor device 60. Computer 98 coordinates operation among the pulse generator 70, data collector 96, and detector 94. In the particular embodiment shown in ~~Figure 3~~ Fig. 6, data collector 96 is electrically connected to semiconductor device 60. In another embodiment, data collector 96 is electrically connected to a point between semiconductor device 60 and switching device 92.